THE DATASHEET OF

ZTX795A

ZTX795A

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C)

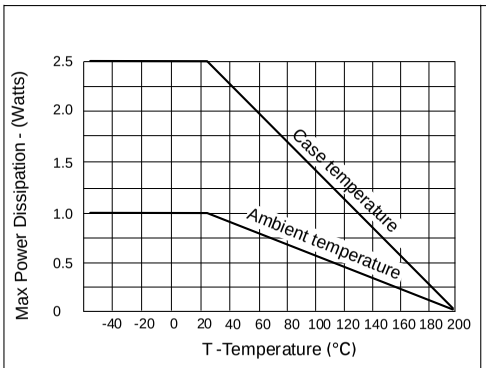
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Transition Frequency	f_T	100			MHz	I_C=-50mA, V_{CE}=-5V f=50MHz
Input Capacitance	C_{ibo}		225		pF	V_{EB}=-0.5V, f=1MHz
Output Capacitance	C_{obo}		15		pF	V_{CB}=-10V, f=1MHz
Switching Times	t_{on} t_{off}		100 1900		ns ns	I_C=-100mA, I_{B1}=-10mA I_{B2}=-10mA, V_{CC}=-50V

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤2%

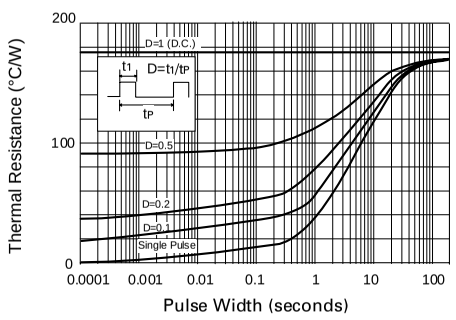
THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance Junction to Ambient$_1$	$R_{th(j\text{-}amb)1}$	175	°C/W
Junction to Ambient$_2$	$R_{th(j\text{-}amb)2}$†	116	°C/W
Junction to Case	$R_{th(j\text{-}case)}$	70	°C/W

† Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.



Derating curve



Maximum transient thermal impedance

PNP SILICON PLANAR ME
HIGH GAIN TRANSISTOR

ISSUE 1 – APRIL 94

FEATURES

* 140 Volt V_{CEO}
* Gain of 250 at I_C=0.2 Amps
* Very low saturation voltage

ABSOLUTE MAXIMUM RATINGS

PARAMETER
Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Peak Pulse Current
Continuous Collector Current
Practical Power Dissipation*
Power Dissipation at T_{amb}=25°C derate above 25°C
Operating and Storage Temperature Ran

*The power which can be dissipated as
P.C.B. with copper equal to 1 inch squa

ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBO
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$
Collector Cut-Off Current	I_{CBO}
Emitter Cut-Off Current	I_{EBO}
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$
Static Forward Current Transfer Ratio	h_{FE}

ZTX795A

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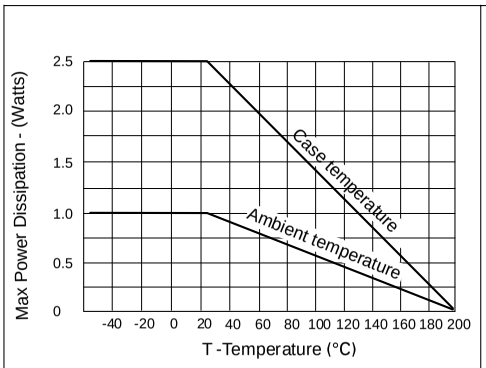

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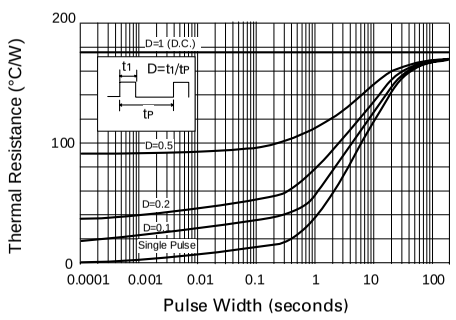

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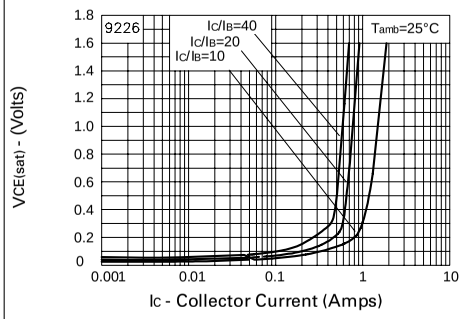
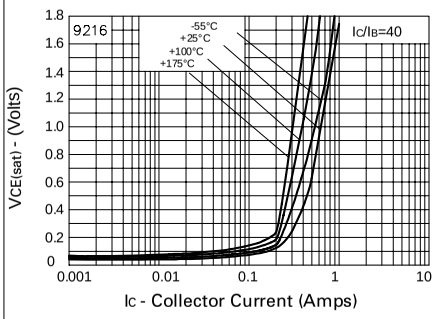
Base-Emitter Saturation Voltage	$V_{BE(sat)}$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$
Static Forward Current Transfer Ratio	h_{FE}

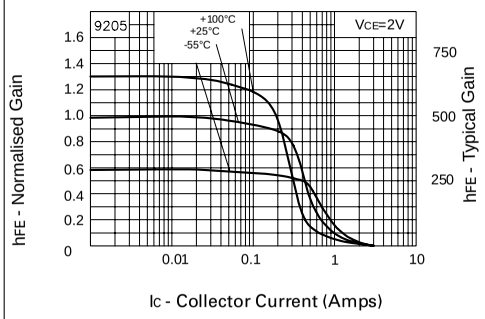
TYPICAL CHARACTERISTICS



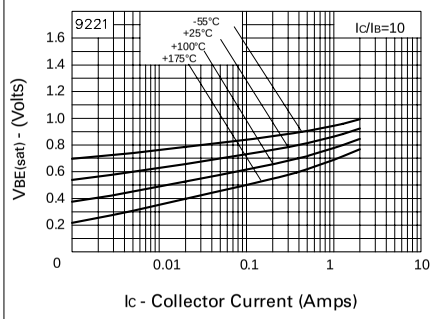
VCE(sat) v IC



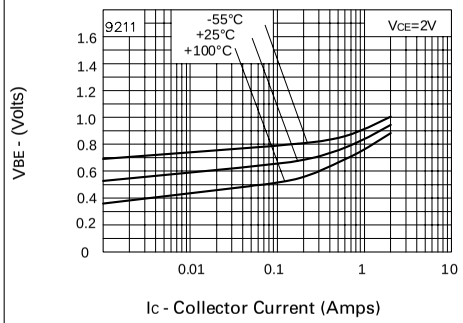
VCE(sat) v IC



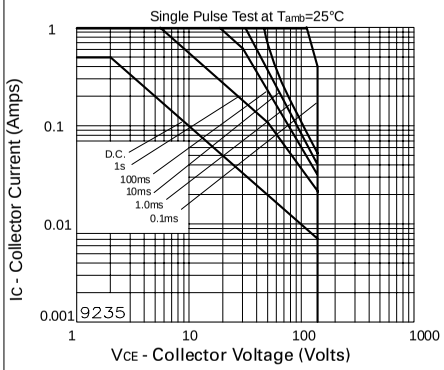
hFE v IC



VBE(sat) v IC



VBE(on) v IC



Safe Operating Area

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